

Application No. 09/992,743


REMARKS

Applicant amends claim 40 by replacing .18Fm with .18 $\mu$ m. The error apparently occurred in connection when applicant converted the document between Word and WordPerfect.

Attached hereto is a marked-up version of the changes made to the above-identified application by the current amendment. The attached page is captioned "Version with markings to show changes made."

Respectfully submitted,

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By   
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DMC/rmw

VERSION WITH MARKINGS TO SHOW CHANGES MADE

40. (Thrice Amended) A process of forming vias and trenches on a semiconductor device that allows for vias and trenches with width of less than about .18 $\mu$ m ~~.18 $\mu$ m~~ and with an aspect ratio of greater than about 6:1 to be substantially filled and substantial filling of large vias and trenches comprising depositing a seed layer of cold aluminum on a metal liner layer, exposing the seed layer to a reactive gas containing atmosphere, and depositing hot aluminum on the seed layer.

RMW IRV1064603.1--4/16/03 10:47 AM